Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type (PCT process)

# 2SC2714

High Frequency Amplifier Applications FM, RF, MIX, IF Amplifier Applications

• Small reverse transfer capacitance:  $C_{re} = 0.7 pF$  (typ.)

• Low noise figure: NF = 2.5dB (typ.)

#### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	40	V
Collector-emitter voltage	V <sub>CEO</sub>	30	V
Emitter-base voltage	V <sub>EBO</sub>	4	V
Collector current	IC	20	mA
Base current	ΙΒ	4	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55 to 125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

1. BASE
2. EMITTER
3. COLLECTOR
S-MINI

JEDEC TO-236

JEITA SC-59

TOSHIBA 2-3F1A

Weight: 12 mg (typ.)

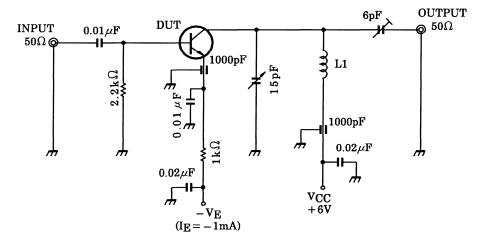
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 40 V, I <sub>E</sub> = 0	_	_	0.5	μΑ
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 4 \text{ V, } I_{C} = 0$			0.5	μА
DC current gain	h <sub>FE</sub> (Note)	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 1 mA	40		200	
Reverse transfer capacitance	C <sub>re</sub>	V <sub>CB</sub> = 6 V, f = 1 MHz	_	0.70		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 1 mA	_	550		MHz
Collector-base time constant	C <sub>c</sub> .rbb'	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 30 \text{ MHz}$	_	_	30	ps
Noise figure	NF	$V_{CC} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz},$	_	2.5	5.0	dB
Power gain	G <sub>pe</sub>	Figure 1	17	23	_	dB

Note: hFE classification R: 40 to 80, O: 70 to 140, Y: 100 to 200

Start of commercial production 1982-10



L1: 0.8 mm<sub>♦</sub> silver plated copper wire, 4T, 10ID, 8 length

Figure1 NF, G<sub>pe</sub> Test Circuit

2

### y Parameter (typ.)

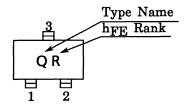
(1) Common emitter ( $V_{CE}$  = 6 V,  $I_{E}$  = -1 mA, f = 100 MHz,  $T_{A}$  = 25°C)

			_
Characteristics	Symbol	Тур.	Unit
Input conductance	9ie	2.9	mS
Input capacitance	C <sub>ie</sub>	10.2	pF
Reverse transfer admittance	y <sub>re</sub>	0.33	mS
Phase angle of reverse transfer admittance	$\theta_{\sf re}$	-90	٥
Forward transfer admittance	lУfel	40	mS
Phase angle of forward transfer admittance	$\theta$ fe	-20	٥
Output conductance	goe	45	μS
Output capacitance	C <sub>oe</sub>	1.1	pF

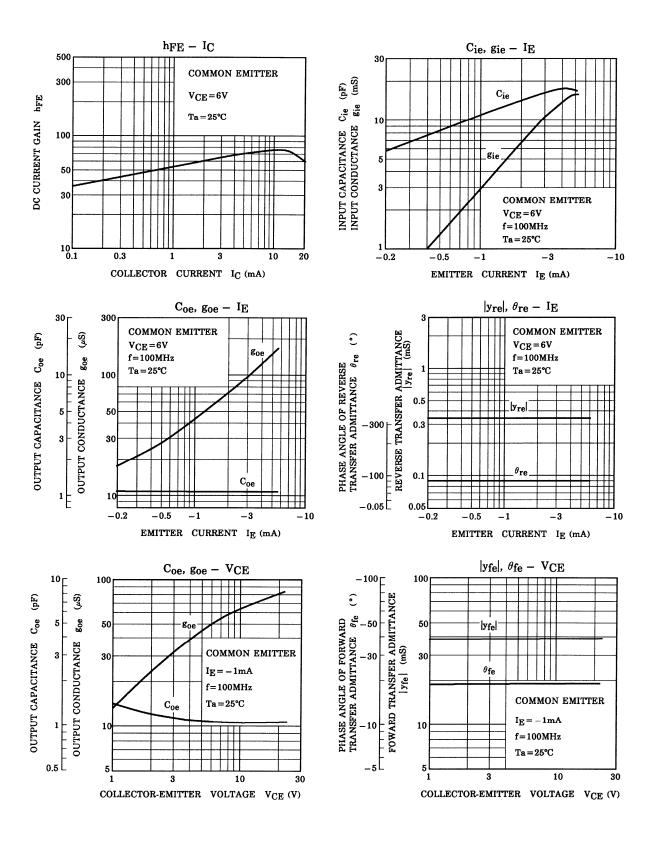
(2) Common base (VCE = 6 V, IE = -1 mA, f = 100 MHz, Ta = 25°C)

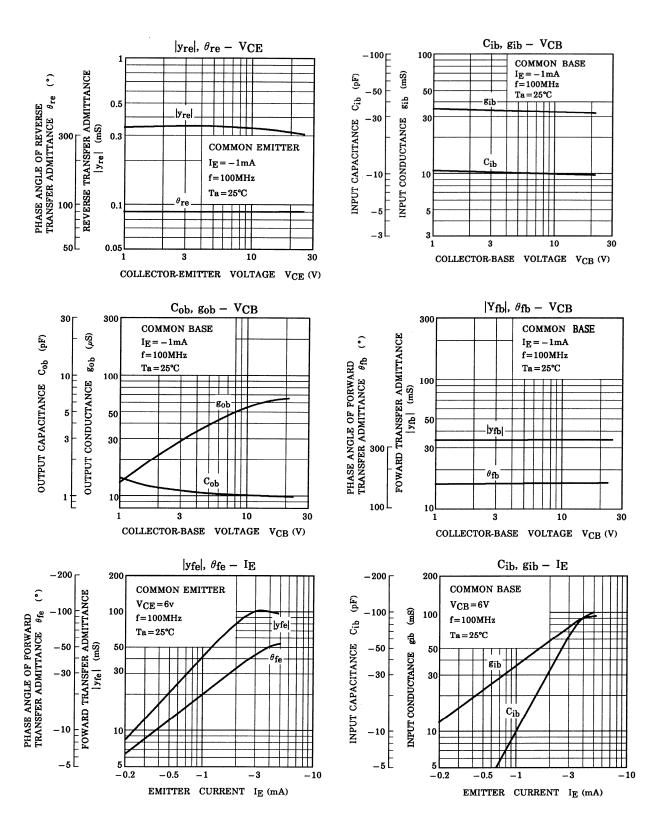
Characteristics	Symbol	Тур.	Unit
Input conductance	9ib	34	mS
Input capacitance	C <sub>ib</sub>	-10	pF
Reverse transfer admittance	y <sub>rb</sub>	0.27	mS
Phase angle of reverse transfer admittance	$\theta_{\sf rb}$	-105	٥
Forward transfer admittance	lу <sub>fb</sub> l	34	mS
Phase angle of forward transfer admittance	$\theta_{fb}$	165	٥
Output conductance	gob	45	μS
Output capacitance	C <sub>ob</sub>	1.1	pF

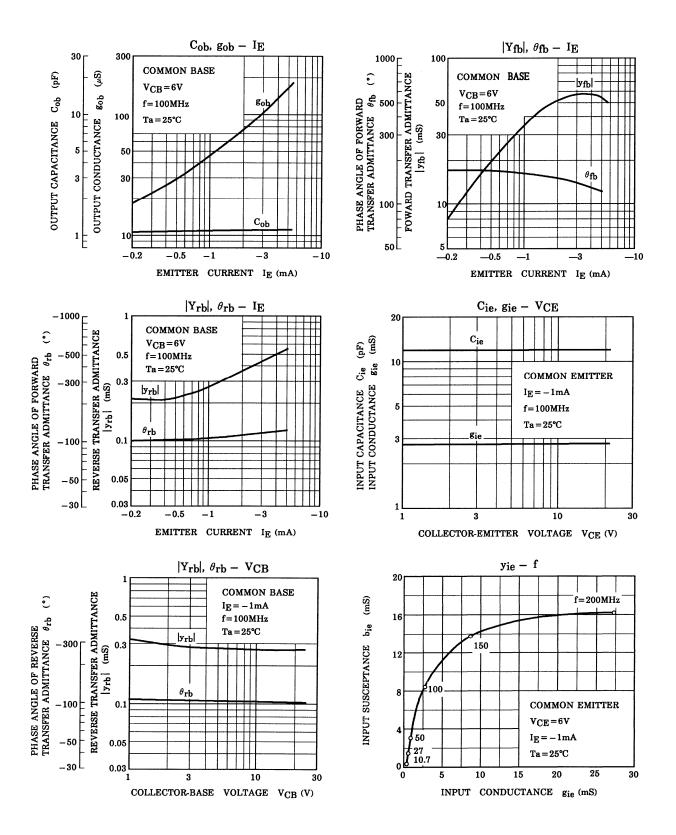
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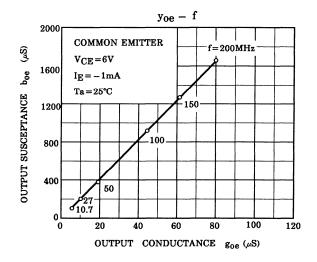


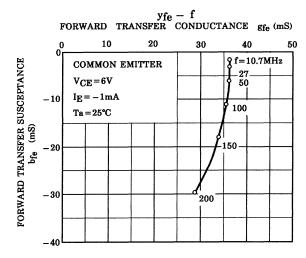
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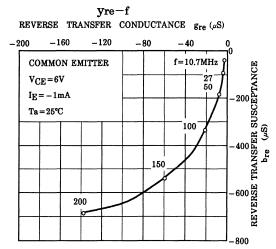


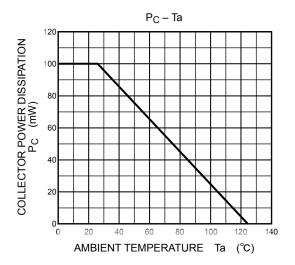












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